



N0118GA

SCR

22 July 2014

Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier with ultra-sensitive gate in a SOT54 (TO-92) plastic package.

2. Features and benefits

- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate

3. Applications

- Electronic ballasts
- Safety shut down and protection circuits
- Sensing circuits
- Smoke detectors
- Switched Mode Power Supplies

4. Quick reference data

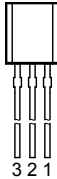

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	-	8	A
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 67\text{ °C}$; Fig. 1	-	-	0.51	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 67\text{ °C}$; Fig. 2 ; Fig. 3	-	-	0.8	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ °C}$; Fig. 7	0.5	-	7	μA



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 <p>TO-92 (SOT54)</p>	
2	G	gate		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

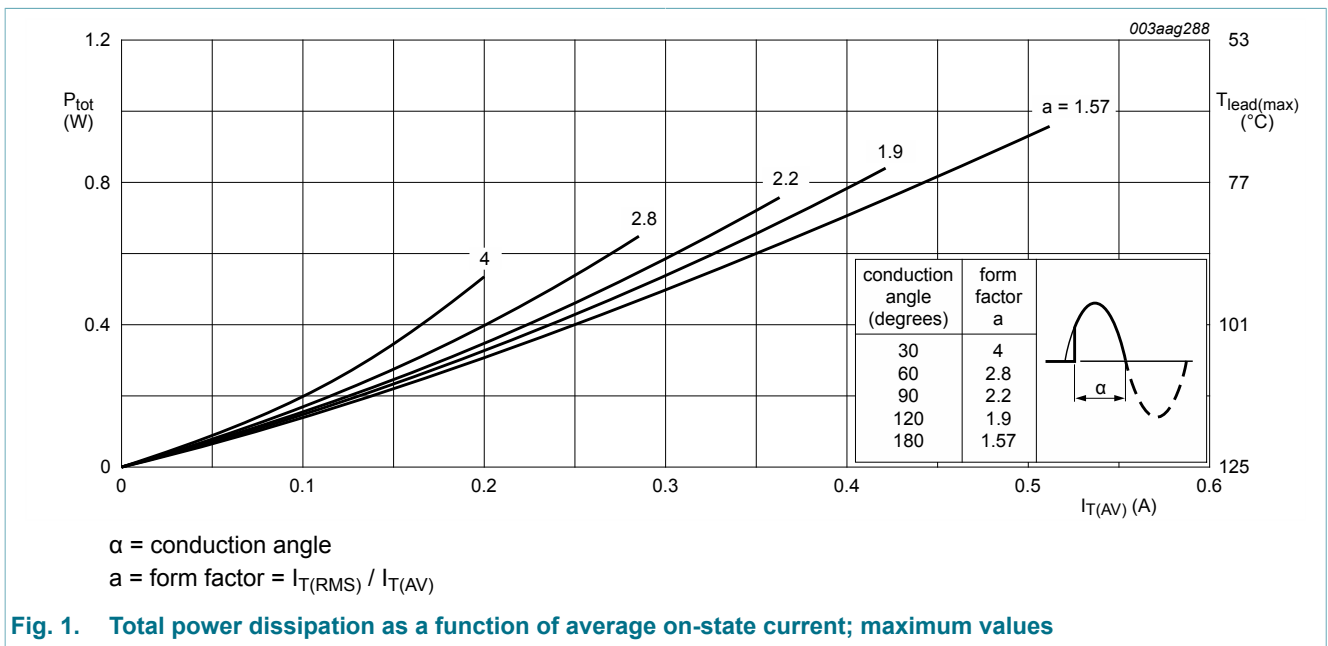
Type number	Package		
	Name	Description	Version
N0118GA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

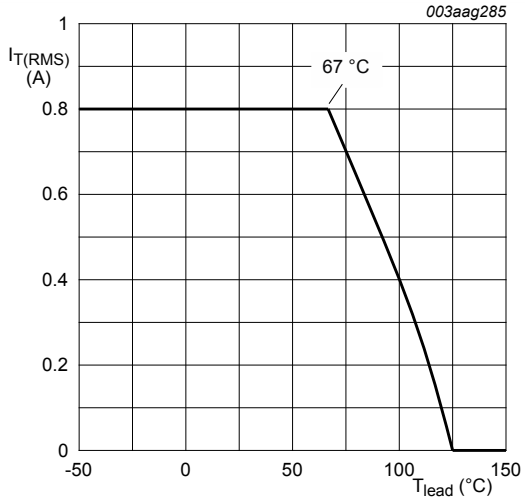
7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

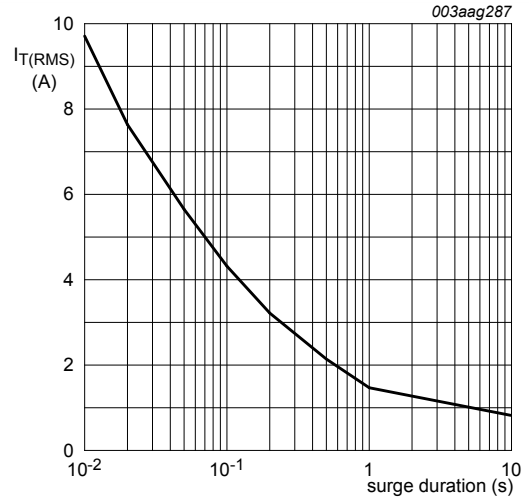
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
V_{RRM}	repetitive peak reverse voltage		-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 67\text{ }^{\circ}\text{C}$; Fig. 1	-	0.51	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 67\text{ }^{\circ}\text{C}$; Fig. 2 ; Fig. 3	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	8	A
		half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	-	9	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	0.32	A^2s
di_T/dt	rate of rise of on-state current	$I_T = 0.8\text{ A}$; $I_G = 10\text{ mA}$; $di_G/dt = 0.1\text{ A}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	1	A
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$





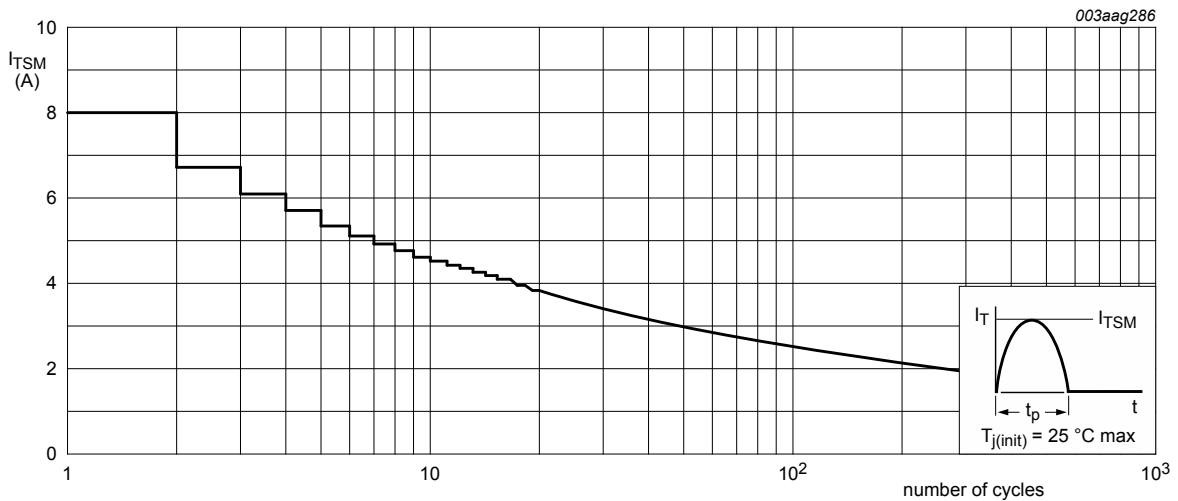
(1) $T_{lead} = 67\text{ °C}$

Fig. 2. RMS on-state current as a function of lead temperature; maximum values



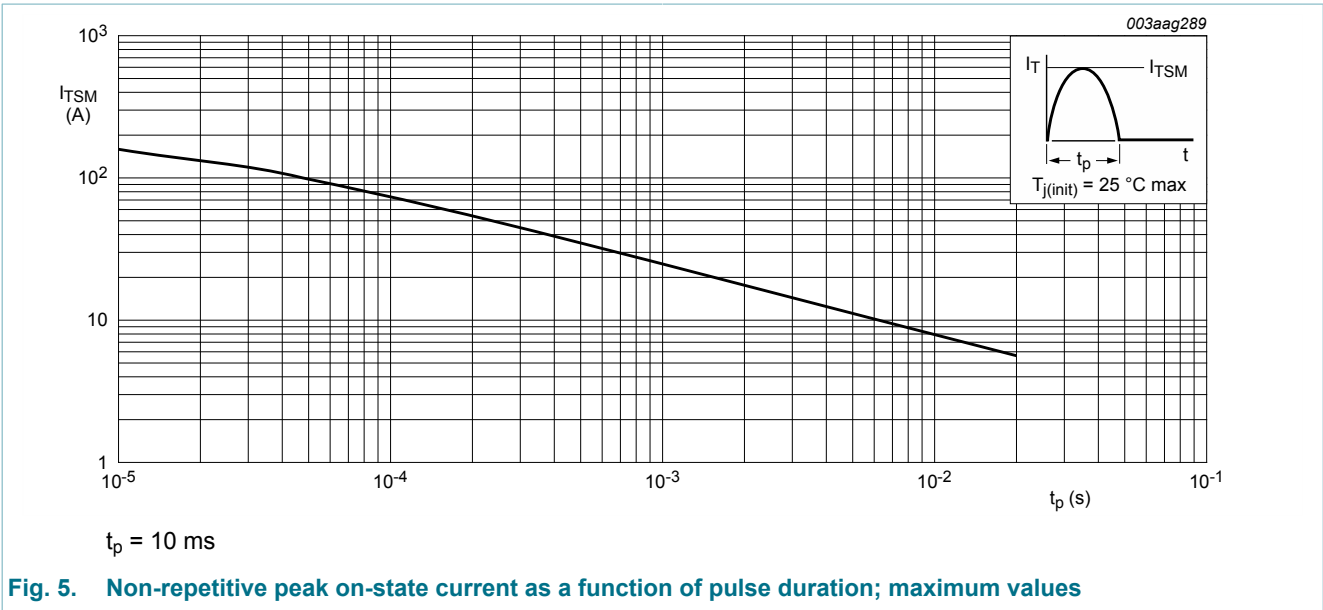
$f = 50\text{ Hz}; T_{lead} = 67\text{ °C}$

Fig. 3. RMS on-state current as a function of surge duration; maximum values



$f = 50\text{ Hz}$

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	Fig. 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

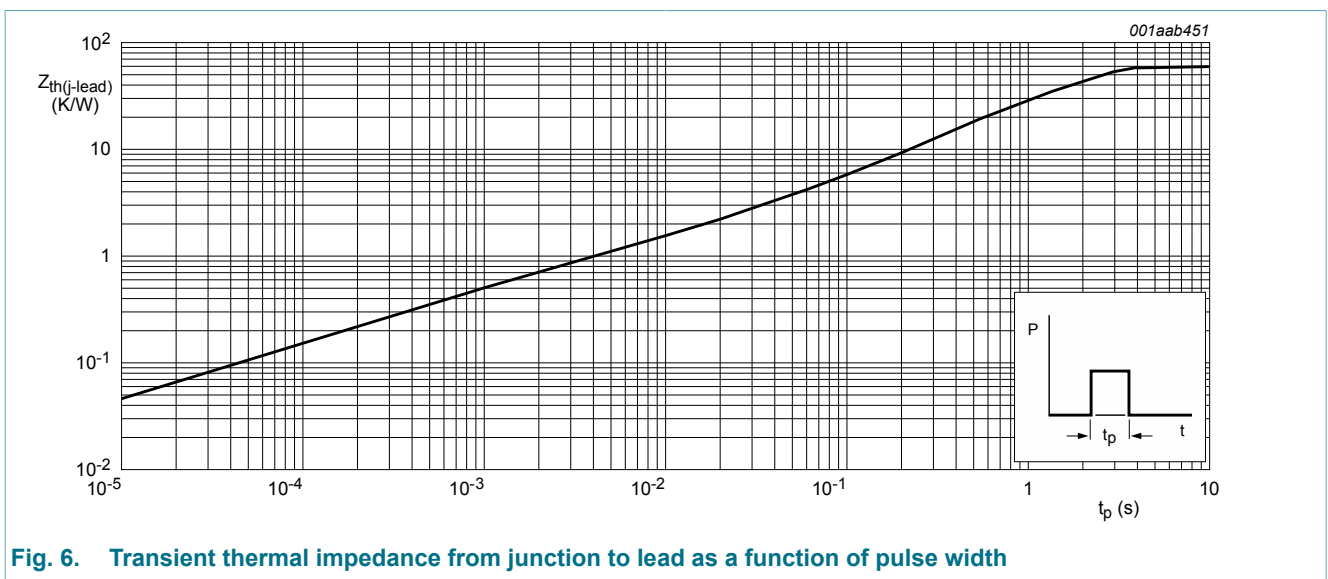


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.5	-	7	μA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	6	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9 ; Fig. 10	-	-	5	mA
V_T	on-state voltage	$I_T = 1.6\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	1.4	1.95	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 12	-	-	0.8	V
I_D	off-state current	$V_D = 400\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	-	-	10	μA
		$V_D = 600\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$	-	-	100	μA
I_R	reverse current	$V_R = 600\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$	-	-	10	μA
		$V_R = 600\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$	-	-	100	μA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 13 ; Fig. 14	75	-	-	$\text{V}/\mu\text{s}$

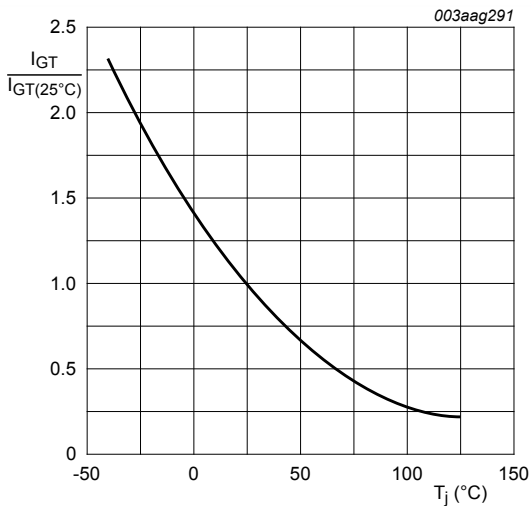
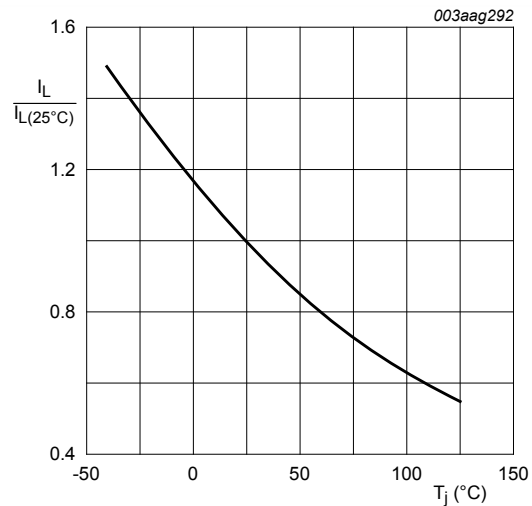
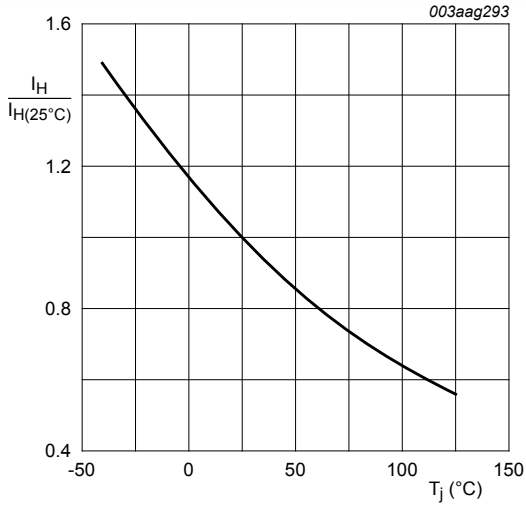


Fig. 7. Normalized gate trigger current as a function of junction temperature



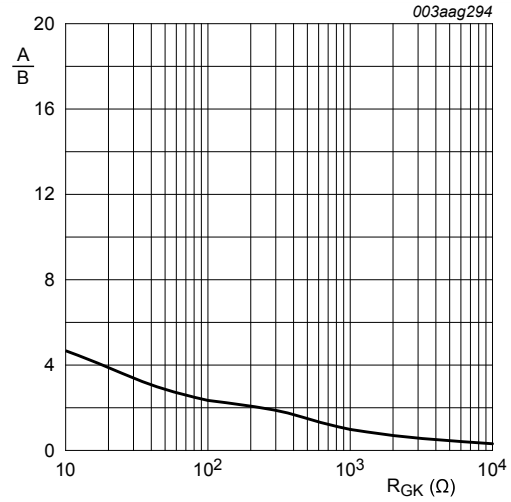
$R_{GK} = 1\text{ k}\Omega$

Fig. 8. Normalized latching current as a function of junction temperature



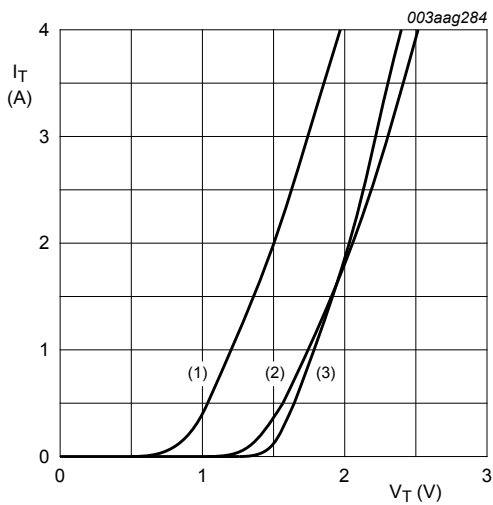
$R_{GK} = 1 \text{ k}\Omega$

Fig. 9. Normalized holding current as a function of junction temperature



$A = I_H [R_{GK}]$
 $B = I_H [R_{GK} = 1 \text{ k}\Omega]$
 $T_j = 25 \text{ }^\circ\text{C}$

Fig. 10. Normalized holding current as a function of gate-cathode resistance (typical values)



$V_o = 1.383 \text{ V}; R_s = 0.4 \text{ }\Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 11. On-state current as a function of on-state voltage

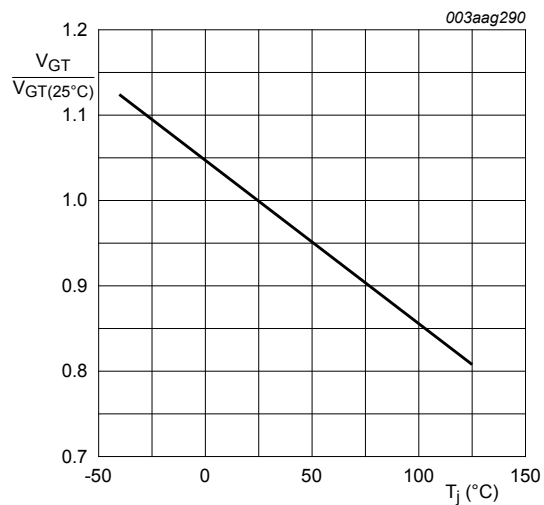
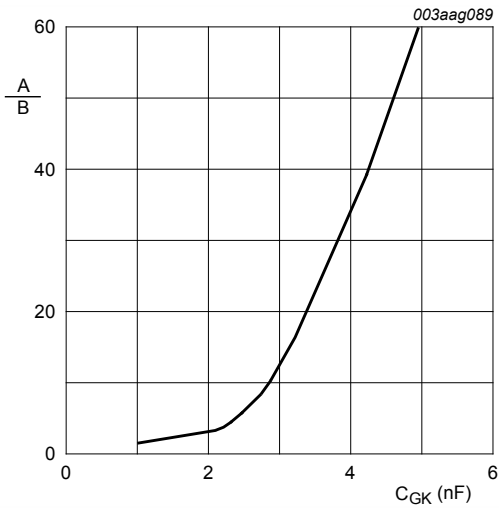
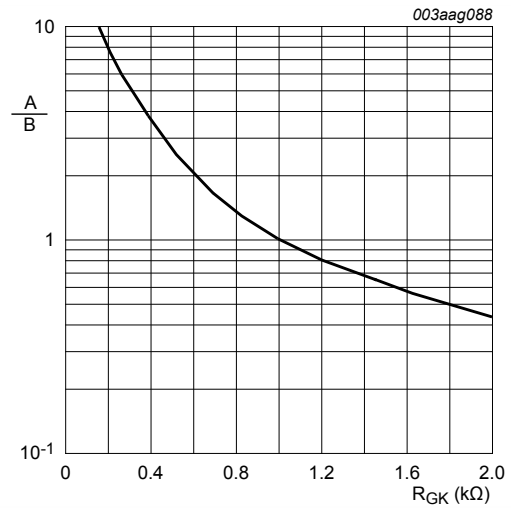


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



$A = dV / dt [C_{GK}]$
 $B = dV / dt [R_{GK} = 1 \text{ k}\Omega]$
 $T_j = 125 \text{ }^\circ\text{C};$
 $R_{GK} = 1 \text{ k}\Omega; V_{DM} = 402 \text{ V}$

Fig. 13. Normalized dVd/dt immunity as a function of gate-cathode capacitance (typical values)



$A = dV / dt [C_{GK}]$
 $B = dV / dt [R_{GK} = 1 \text{ k}\Omega]$
 $T_j = 125 \text{ }^\circ\text{C};$
 $R_{GK} = 1 \text{ k}\Omega; V_{DM} = 402 \text{ V}$

Fig. 14. Normalized dVd/dt immunity as a function of gate-cathode resistance (typical values)

10. Package outline



Fig. 15. Package outline TO-92 (SOT54)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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12. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	3
8	Thermal characteristics	6
9	Characteristics	7
10	Package outline	10
11	Legal information	11
11.1	Data sheet status	11
11.2	Definitions	11
11.3	Disclaimers	11
11.4	Trademarks	12

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